NEC

MOS INTEGRATED CIRCUIT

μPD42S4800L, 424800L

3.3 V OPERATION 4 M-BIT DYNAMIC RAM 512 K-WORD BY 8-BIT, FAST PAGE MODE

Description

The μPD42S4800L, 424800L are 524 288 words by 8 bits dynamic CMOS RAMs. The fast page mode capability realize high speed access and low power consumption.

Besides, the μPD42S4800L can execute $\overline{CAS}$ before $\overline{RAS}$ self refresh.

These devices are packed in 28-pin plastic TSOP(II) and 28-pin plastic SOJ.

Features

- 524 288 words by 8 bits organization
- Single +3.3 V ± 0.3 V power supply
- Fast access and cycle time

Part number	Power consumption Active (MAX.)	Access time (MAX.)	R/W cycle time (MIN.)	Fast page mode cycle time (MIN.)
μPD42S4800L-A70, 424800L-A70	288 mW	70 ns	130 ns	45 ns
μPD42S4800L-A80, 424800L-A80	252 mW	80 ns	150 ns	50 ns

- The μPD42S4800L can execute $\overline{CAS}$ before $\overline{RAS}$ self refresh

Part number	Refresh cycle	Refresh	Power consumption at standby (MAX.)
μPD42S4800L	1 024 cycles/128 ms	$\overline{CAS}$ before $\overline{RAS}$ self refresh, $\overline{CAS}$ before $\overline{RAS}$ refresh, $\overline{RAS}$ only refresh, Hidden refresh	0.36 mW (CMOS level input)
μPD424800L	1 024 cycles/16 ms	$\overline{CAS}$ before $\overline{RAS}$ refresh, $\overline{RAS}$ only refresh, Hidden refresh	1.8 mW (CMOS level input)

- Multiplexed address inputs ··· Row address : A0 to A9, Column address : A0 to A8

Ordering Information

Part number	Access time (MAX.)	Package	Refresh
μPD42S4800LG5-A70	70 ns	28-pin Plastic TSOP (II) (400 mil)	$\overline{CAS}$ before $\overline{RAS}$ self refresh $\overline{CAS}$ before $\overline{RAS}$ refresh $\overline{RAS}$ only refresh Hidden refresh
μPD42S4800LG5-A80	80 ns		
μPD42S4800LG5-A70-7KD	70 ns	28-pin Plastic TSOP(II) (400 mil) Reverse bent	
μPD42S4800LG5-A80-7KD	80 ns		
μPD42S4800LG5-A10-7KD	100 ns		
μPD42S4800LLE-A70	70 ns	28-pin Plastic SOJ (400 mil)	
μPD42S4800LLE-A80	80 ns		
μPD424800LG5-A70	70 ns	28-pin Plastic TSOP (II) (400 mil)	$\overline{CAS}$ before $\overline{RAS}$ refresh $\overline{RAS}$ only refresh Hidden refresh
μPD424800LG5-A80	80 ns		
μPD424800LG5-A70-7KD	70 ns	28-pin Plastic TSOP (II) (400 mil) Reverse bent	
μPD424800LG5-A80-7KD	80 ns		
μPD424800LG5-A10-7KD	100 ns		
μPD424800LLE-A70	70 ns	28-pin Plastic SOJ (400 mil)	
μPD424800LLE-A80	80 ns		

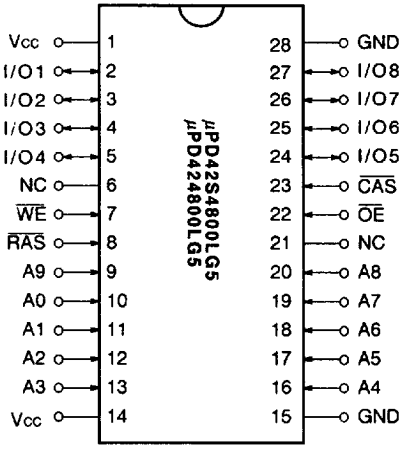
Quality Grade

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

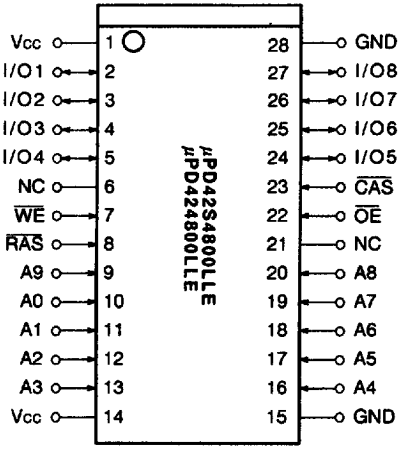
Pin Configurations (Marking side)

28-pin Plastic TSOP(II)
(400 mil)



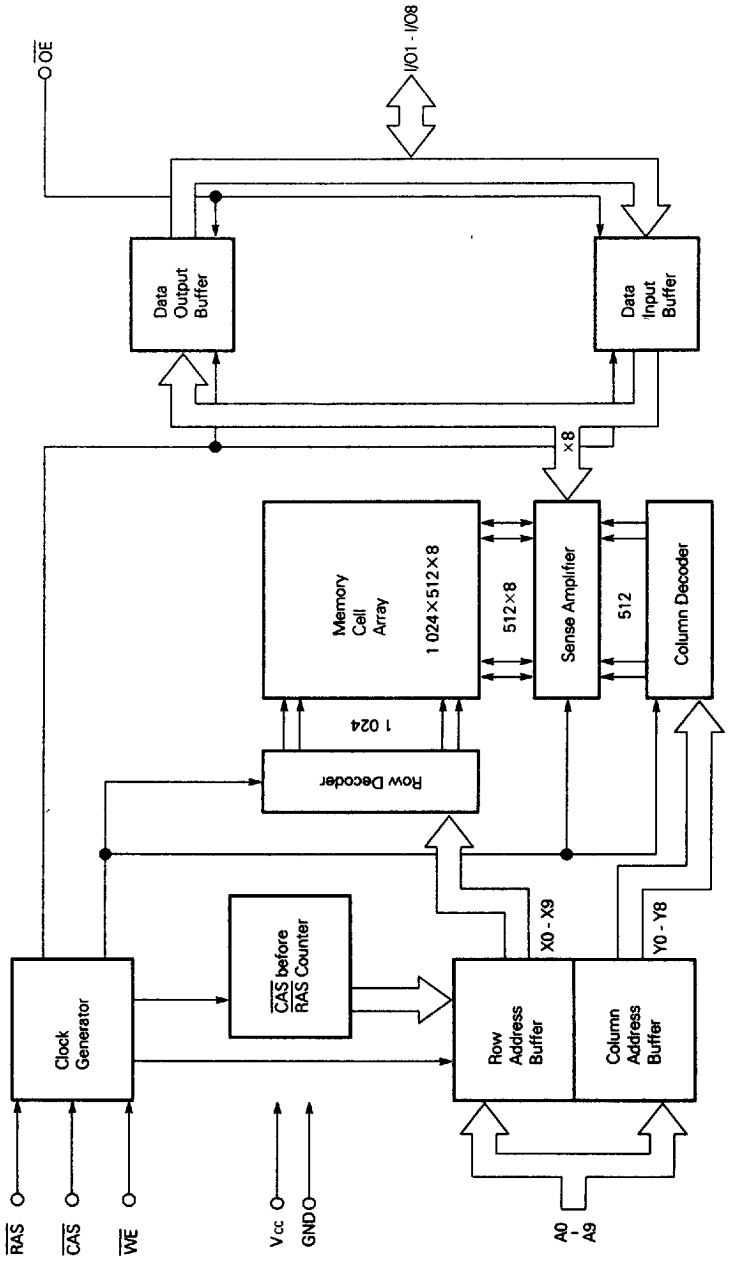
A0 to A9	: Address Inputs
I/O1 to I/O8	: Data Inputs/Outputs
$\overline{RAS}$	: Row Address Strobe
$\overline{CAS}$	: Column Address Strobe
$\overline{WE}$	: Write Enable
$\overline{OE}$	: Output Enable
Vcc	: Power Supply
GND	: Ground
NC	: No Connection

28-pin Plastic SOJ
(400 mil)



A0 to A9	: Address Inputs
I/O1 to I/O8	: Data Inputs/Outputs
$\overline{RAS}$	: Row Address Strobe
$\overline{CAS}$	: Column Address Strobe
$\overline{WE}$	: Write Enable
$\overline{OE}$	: Output Enable
Vcc	: Power Supply
GND	: Ground
NC	: No Connection

Block Diagram



Input/Output Pin Functions

The μPD42S4800L, 424800L have input pins $\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$, A0 to A9 and input/output pins I/O1 to I/O8.

Pin name	Input/ Output	Function
$\overline{RAS}$ (Row address strobe)	Input	$\overline{RAS}$ activates the sense amplifier by latching a row address (A0 to A9) and selecting a corresponding word line. It refreshes memory cell array of one line (4 096-bit) selected by the row address (A0 to A9). It also selects the following function. • $\overline{CAS}$ before $\overline{RAS}$ refresh
$\overline{CAS}$ (Column address strobe)	Input	$\overline{CAS}$ activates data input/output circuit by latching column address (A0 to A8) and selecting a digit line connected with the sense amplifier.
A0 to A9 (Address inputs)	Input	10-bit address bus. Input total 19-bit of address signal, upper 10-bit and lower 9-bit in sequence (address multiplex method). Therefore, one word (8-bit) is selected from 524 288-word by 8-bit memory cell array. In actual operation, latch row address by specifying row address and activating $\overline{RAS}$. Then, switch the address bus to column address and activate $\overline{CAS}$. Each address is taken into the device when $\overline{RAS}$ and $\overline{CAS}$ are activated. Therefore, the address input setup time (t_{ASR}, t_{ASC}) and hold time (t_{RAH}, t_{CAH}) are specified for the activation of $\overline{RAS}$ and $\overline{CAS}$.
$\overline{WE}$ (Write enable)	Input	Write control signal. Write operation is executed by activating $\overline{RAS}$, $\overline{CAS}$ and $\overline{WE}$.
$\overline{OE}$ (Output enable)	Input	Read control signal. Read operation can be executed by activating $\overline{RAS}$, $\overline{CAS}$ and $\overline{OE}$. If $\overline{WE}$ is activated during read operation, $\overline{OE}$ is to be ineffective in the device. Therefore, read operation cannot be executed.
I/O1 to I/O8 (Data inputs / outputs)	Input/ Output	8-bit data bus. I/O1 to I/O8 are used to input/output data.

Electrical Specifications

- All voltages are referenced to GND.
- After power up, wait more than 100 μs and then, execute eight $\overline{CAS}$ before RAS or $\overline{RAS}$ only refresh cycles as dummy cycles to initialize internal circuit.

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Voltage on Any Pin Relative to GND	V_T		−0.5 to +4.6	V
Supply Voltage	V_{CC}		−0.5 to +4.6	V
Output Current	I_O		20	mA
Power Dissipation	P_D		1	W
Operating Temperature	T_{opt}		0 to +70	°C
Storage Temperature	T_{stg}		−55 to +125	°C

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply Voltage	V_{CC}		3.0	3.3	3.6	V
High Level Input Voltage	V_{IH}		2.0		V_{CC} +0.3	V
Low Level Input Voltage	V_{IL}		−0.3		+0.8	V
Ambient Temperature	T_a		0		70	°C

Capacitance (T_a = 25 °C, f = 1 MHz)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Input Capacitance	C_{I1}	Address			5	pF
	C_{I2}	$\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$			7	pF
Data Input/Output Capacitance	$C_{I/O}$	I/O			7	pF

DC Characteristics (Recommended operating conditions unless otherwise noted)

Parameter		Symbol	Test Condition		MIN.	TYP.	MAX.	Unit	Notes
Operating current		I_{CC1}	$\overline{RAS}$, $\overline{CAS}$ Cycling $t_{RC} = t_{RC(MIN)}$ I_O = 0 mA	t_{RAC} = 70 ns t_{RAC} = 80 ns			80 70	mA	1, 2, 3
Standby current	μPD42S4800L	I_{CC2}	$\overline{RAS}$, $\overline{CAS} \geqq V_{IH(MIN)}$, I_O = 0 mA				0.5	mA	
			$\overline{RAS}$, $\overline{CAS} \geqq V_{CC} - 0.2$ V, I_O = 0 mA				0.1		
	μPD424800L		$\overline{RAS}$, $\overline{CAS} \geqq V_{IH(MIN)}$, I_O = 0 mA				2		
			$\overline{RAS}$, $\overline{CAS} \geqq V_{CC} - 0.2$ V, I_O = 0 mA				0.5		
$\overline{RAS}$ only refresh current		I_{CC3}	$\overline{RAS}$ Cycling, $\overline{CAS} \geqq V_{IH(MIN)}$ $t_{RC} = t_{RC(MIN)}$, I_O = 0 mA	t_{RAC} = 70 ns t_{RAC} = 80 ns			80 70	mA	1,2,3,4
Operating current (Fast page mode)		I_{CC4}	$\overline{RAS} \leqq V_{IL(MAX)}$, $\overline{CAS}$ Cycling $t_{PC} = t_{PC(MIN)}$, I_O = 0 mA	t_{RAC} = 70 ns t_{RAC} = 80 ns			70 60	mA	1, 2, 5
$\overline{CAS}$ before $\overline{RAS}$ refresh current		I_{CC5}	$\overline{RAS}$ Cycling $t_{RC} = t_{RC(MIN.)}$ I_O = 0 mA	t_{RAC} = 70 ns t_{RAC} = 80 ns			80 70	mA	1, 2
$\overline{CAS}$ before $\overline{RAS}$ long refresh current (1 024 Cycles / 128 ms, only for the μPD42S4800L)		I_{CC6}	$\overline{CAS}$ before $\overline{RAS}$ refresh : 1 024 Cycles / 128 ms $\overline{RAS}$, $\overline{CAS}$: V_{CC}–0.2 V ≦ $V_{IH} \leqq V_{IH(MAX.)}$ 0 V ≦ $V_{IL} \leqq$ 0.2 V	$t_{RAS} \leqq$ 200 ns			100	μA	1, 2
			Standby : $\overline{RAS}$, $\overline{CAS} \geqq V_{CC}$–0.2 V Address : V_{IH} or V_{IL} $\overline{WE}$, $\overline{OE}$: V_{IH} I_O = 0 mA	$t_{RAS} \leqq$ 1 μs			150		
Self refresh current ($\overline{CAS}$ before $\overline{RAS}$ self refresh, only for the μPD42S4800L)		I_{CC7}	$\overline{RAS}$, $\overline{CAS}$: V_{CC}–0.2 V ≦ $V_{IH} \leqq V_{IH(MAX.)}$ 0 V ≦ $V_{IL} \leqq$ 0.2 V I_O = 0 mA				100	μA	2
Input leakage current		$I_{I(L)}$	V_I = 0 to 3.6 V All other pins not under test = 0 V		–5		+5	μA	
Output leakage current		$I_{O(L)}$	V_O = 0 to 3.6 V Output is disabled (Hi-Z)		–5		+5	μA	
High level output voltage		V_{OH}	I_O = –2.0 mA		2.4			V	
Low level output voltage		V_{OL}	I_O = +2.0 mA				0.4	V	

Notes 1. I_{CC1}, I_{CC3}, I_{CC4}, I_{CC5} and I_{CC6} depend on cycle rates (t_{RC} and t_{PC}).

2. Specified values are obtained with outputs unloaded.

3. I_{CC1} and I_{CC3} are measured assuming that address can be changed once or less during $\overline{RAS} \leqq V_{IL(MAX.)}$ and $\overline{CAS} \geqq V_{IH(MIN.)}$.

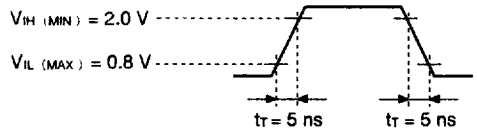
4. I_{CC3} is measured assuming that all column address inputs are held at either high or low.

5. I_{CC4} is measured assuming that all column address inputs are switched only once during each fast page cycle.

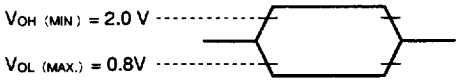
AC Characteristics (Recommended Operating Conditions unless otherwise noted)

AC Characteristics Test Conditions

(1) Input timing specification



(2) Output timing specification



(3) Loading conditions are 100 pF + 1 TTL.

Common to Read, Write, Read Modify Write Cycle

Parameter		Symbol	tRAC = 70 ns		tRAC = 80 ns		Unit	Notes
			MIN.	MAX.	MIN.	MAX.		
Read / Write Cycle Time		tRC	130	–	150	–	ns	
$\overline{RAS}$ Precharge Time		tRP	50	–	60	–	ns	
$\overline{CAS}$ Precharge Time		tCPN	10	–	10	–	ns	
$\overline{RAS}$ Pulse Width		tRAS	70	10 000	80	10 000	ns	
$\overline{CAS}$ Pulse Width		tCAS	20	10 000	20	10 000	ns	
$\overline{RAS}$ Hold Time		tRSH	20	–	20	–	ns	
$\overline{CAS}$ Hold Time		tCSH	70	–	80	–	ns	
$\overline{RAS}$ to $\overline{CAS}$ Delay Time		tRCD	20	50	20	60	ns	1
$\overline{RAS}$ to Column Address Delay Time		tRAD	15	35	15	40	ns	1
$\overline{CAS}$ to $\overline{RAS}$ Precharge Time		tCRP	10	–	10	–	ns	2
Row Address Setup Time		tASR	0	–	0	–	ns	
Row Address Hold Time		tRAH	10	–	10	–	ns	
Column Address Setup Time		tASC	0	–	0	–	ns	
Column Address Hold Time		tCAH	15	–	15	–	ns	
$\overline{OE}$ Lead Time Referenced to $\overline{RAS}$		tOES	0	–	0	–	ns	
$\overline{CAS}$ to Data Setup Time		tCLZ	0	–	0	–	ns	
$\overline{OE}$ to Data Setup Time		tOLZ	0	–	0	–	ns	
$\overline{OE}$ to Data Delay Time		tOED	15	–	15	–	ns	
Transition Time (Rise and Fall)		tT	3	50	3	50	ns	
Refresh Time	μPD42S4800L	tREF	–	128	–	128	ms	3
	μPD424800L		–	16	–	16	ms	

Notes 1. For read cycles, access time is defined as follows:

Input Conditions	Access Time	Access Time from $\overline{RAS}$
$t_{RAD} \leqq t_{RAD(MAX.)}$ and $t_{RCD} \leqq t_{RCD(MAX.)}$	$t_{RAC(MAX.)}$	$t_{RAC(MAX.)}$
$t_{RAD} > t_{RAD(MAX.)}$ and $t_{RCD} \leqq t_{RCD(MAX.)}$	$t_{AA(MAX.)}$	$t_{RAD} + t_{AA(MAX.)}$
$t_{RCD} > t_{RCD(MAX.)}$	$t_{CAC(MAX.)}$	$t_{RCD} + t_{CAC(MAX.)}$

$t_{RAD(MAX.)}$ and $t_{RCD(MAX.)}$ are specified as reference points only ; they are not restrictive operating parameters. They are used to determine which access time(t_{RAC}, t_{AA} or t_{CAC}) is to be used for finding out when output data will be available. Therefore, the input conditions $t_{RAD} \geqq t_{RAD(MAX.)}$ and $t_{RCD} \geqq t_{RCD(MAX.)}$ will not cause any operation problems.

2. $t_{CRP(MIN.)}$ requirement is applied for $\overline{RAS}$, $\overline{CAS}$ cycles preceded by any cycle.
3. This specification is applied only for the μPD42S4800L.

Read Cycle

Parameter	Symbol	t_{RAC} = 70 ns		t_{RAC} = 80 ns		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
Access Time from $\overline{RAS}$	t_{RAC}	–	70	–	80	ns	1
Access Time from $\overline{CAS}$	t_{CAC}	–	20	–	20	ns	1
Access Time from Column Address	t_{AA}	–	35	–	40	ns	1
Access Time from $\overline{OE}$	t_{OEA}	–	20	–	20	ns	
Column Address Lead Time Referenced to $\overline{RAS}$	t_{RAL}	35	–	40	–	ns	
Read Command Setup Time	t_{RCS}	0	–	0	–	ns	
Read Command Hold Time Referenced to $\overline{RAS}$	t_{RRH}	0	–	0	–	ns	2
Read Command Hold Time Referenced to $\overline{CAS}$	t_{RCH}	0	–	0	–	ns	2
Output Buffer Turn-off Delay Time from $\overline{OE}$	t_{OEZ}	0	15	0	15	ns	3
Output Buffer Turn-off Delay Time from $\overline{CAS}$	t_{OFF}	0	15	0	15	ns	3

Notes 1. For read cycles, access time is defined as follows:

Input Conditions	Access Time	Access Time from $\overline{RAS}$
$t_{RAD} \leqq t_{RAD(MAX.)}$ and $t_{RCD} \leqq t_{RCD(MAX.)}$	$t_{RAC(MAX.)}$	$t_{RAC(MAX.)}$
$t_{RAD} > t_{RAD(MAX.)}$ and $t_{RCD} \leqq t_{RCD(MAX.)}$	$t_{AA(MAX.)}$	$t_{RAD} + t_{AA(MAX.)}$
$t_{RCD} > t_{RCD(MAX.)}$	$t_{CAC(MAX.)}$	$t_{RCD} + t_{CAC(MAX.)}$

$t_{RAD(MAX.)}$ and $t_{RCD(MAX.)}$ are specified as reference points only ; they are not restrictive operating parameters. They are used to determine which access time(t_{RAC}, t_{AA} or t_{CAC}) is to be used for finding out when output data will be available. Therefore, the input conditions $t_{RAD} \geqq t_{RAD(MAX.)}$ and $t_{RCD} \geqq t_{RCD(MAX.)}$ will not cause any operation problems.

2. Either $t_{RCH(MIN.)}$ or $t_{RRH(MIN.)}$ should be met in read cycles.
3. $t_{OFF(MAX.)}$ and $t_{OEZ(MAX.)}$ define the time when the output achieves the condition of Hi - Z and is not referenced to V_{OH} or V_{OL}.

Write Cycle

Parameter	Symbol	t_{RAC} = 70 ns		t_{RAC} = 80 ns		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
$\overline{WE}$ Hold Time Referenced to $\overline{CAS}$	t_{WCH}	10	–	15	–	ns	1
$\overline{WE}$ Pulse Width	t_{WP}	10	–	15	–	ns	1
$\overline{WE}$ Lead Time Referenced to $\overline{RAS}$	t_{RWL}	20	–	20	–	ns	
$\overline{WE}$ Lead Time Referenced to $\overline{CAS}$	t_{CWL}	15	–	15	–	ns	
$\overline{WE}$ Setup Time	t_{WCS}	0	–	0	–	ns	2
$\overline{OE}$ Hold Time	t_{OEH}	0	–	0	–	ns	
Data-in Setup Time	t_{DS}	0	–	0	–	ns	3
Data-in Hold Time	t_{DH}	15	–	15	–	ns	3

Notes 1. $t_{WP(MIN)}$ is applied for late write cycles or read modify write cycles. In early write cycles, $t_{WCH(MIN)}$ should be met.

2. If $t_{WCS} \geqq t_{WCS(MIN)}$, the cycle is an early write cycle and the data out will remain Hi - Z through the entire cycle.

3. $t_{DS(MIN.)}$ and $t_{DH(MIN)}$ are referenced to the $\overline{CAS}$ falling edge in early write cycles. In late write cycles and read modify write cycles, they are referenced to the $\overline{WE}$ falling edge.

Read Modify Write Cycle

Parameter	Symbol	t_{RAC} = 70 ns		t_{RAC} = 80 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.		
Read Modify Write Cycle Time	t_{RWC}	175	–	200	–	ns	
$\overline{RAS}$ to $\overline{WE}$ Delay Time	t_{RWD}	90	–	105	–	ns	1
$\overline{CAS}$ to $\overline{WE}$ Delay Time	t_{CWD}	40	–	45	–	ns	1
Column Address to $\overline{WE}$ Delay Time	t_{AWD}	55	–	65	–	ns	1

Note 1. If $t_{WCS} \geqq t_{WCS(MIN)}$, the cycle is an early write cycle and the data out will remain Hi - Z through the entire cycle. If $t_{RWD} \geqq t_{RWD(MIN.)}$, $t_{CWD} \geqq t_{CWD(MIN.)}$, $t_{AWD} \geqq t_{AWD(MIN)}$, and $t_{CPWD} \geqq t_{CPWD(MIN.)}$, the cycle is a read modify write cycle and the data out will contain data read from the selected cell. If neither of the above conditions is met, the state of the data out is indeterminate.

Fast Page Mode

Parameter	Symbol	t_{RAC} = 70 ns		t_{RAC} = 80 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.		
Fast Page Mode Cycle Time	t_{PC}	45	–	50	–	ns	
Access Time from $\overline{CAS}$ Precharge	t_{ACP}	–	40	–	45	ns	
$\overline{RAS}$ Pulse Width	t_{RASP}	70	125 000	80	125 000	ns	
$\overline{CAS}$ Precharge Time	t_{CP}	10	–	10	–	ns	
$\overline{RAS}$ Hold Time from $\overline{CAS}$ Precharge	t_{RHCP}	40	–	45	–	ns	
Read Modify Write Cycle Time	t_{PRWC}	90	–	100	–	ns	
$\overline{CAS}$ Precharge to $\overline{WE}$ Delay Time	t_{CPWD}	60	–	70	–	ns	1

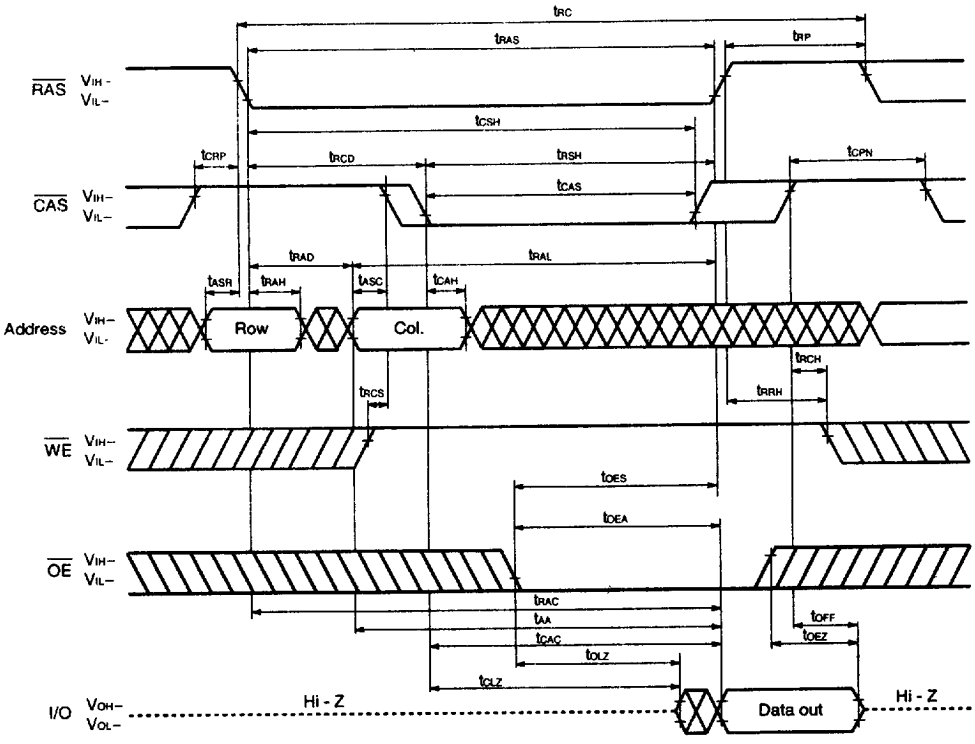
Note 1. If $t_{WCS} \geqq t_{WCS(MIN.)}$, the cycle is an early write cycle and the data out will remain Hi - Z through the entire cycle. If $t_{RWD} \geqq t_{RWD(MIN.)}$, $t_{CWD} \geqq t_{CWD(MIN.)}$, $t_{AWD} \geqq t_{AWD(MIN.)}$, and $t_{CPWD} \geqq t_{CPWD(MIN.)}$, the cycle is a read modify write cycle and the data out will contain data read from the selected cell. If neither of the above conditions is met, the state of the data out is indeterminate.

Refresh Cycle

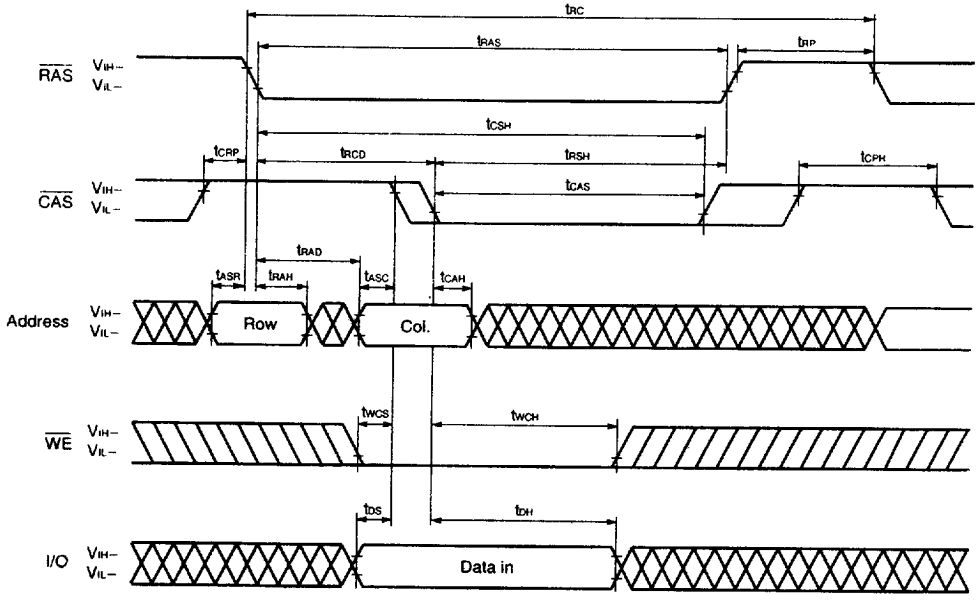
Parameter	Symbol	t_{RAC} = 70 ns		t_{RAC} = 80 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.		
$\overline{CAS}$ Setup Time	t_{CSR}	5	–	5	–	ns	
$\overline{CAS}$ Hold Time ($\overline{CAS}$ before $\overline{RAS}$ Refresh)	t_{CHR}	10	–	10	–	ns	
$\overline{RAS}$ Precharge $\overline{CAS}$ Hold Time	t_{RPC}	10	–	10	–	ns	
$\overline{RAS}$ Pulse Width ($\overline{CAS}$ before $\overline{RAS}$ Self Refresh Cycle)	t_{RASS}	100	–	100	–	μs	1
$\overline{RAS}$ Precharge Time ($\overline{CAS}$ before $\overline{RAS}$ Self Refresh Cycle)	t_{RPS}	130	–	150	–	ns	1
$\overline{CAS}$ Hold Time ($\overline{CAS}$ before $\overline{RAS}$ Self Refresh Cycle)	t_{CHS}	-50	–	-50	–	ns	1
$\overline{WE}$ Hold Time	t_{WHR}	15	–	15	–	ns	

Note 1. This specification is applied only for the μPD42S4800L.

Read Cycle

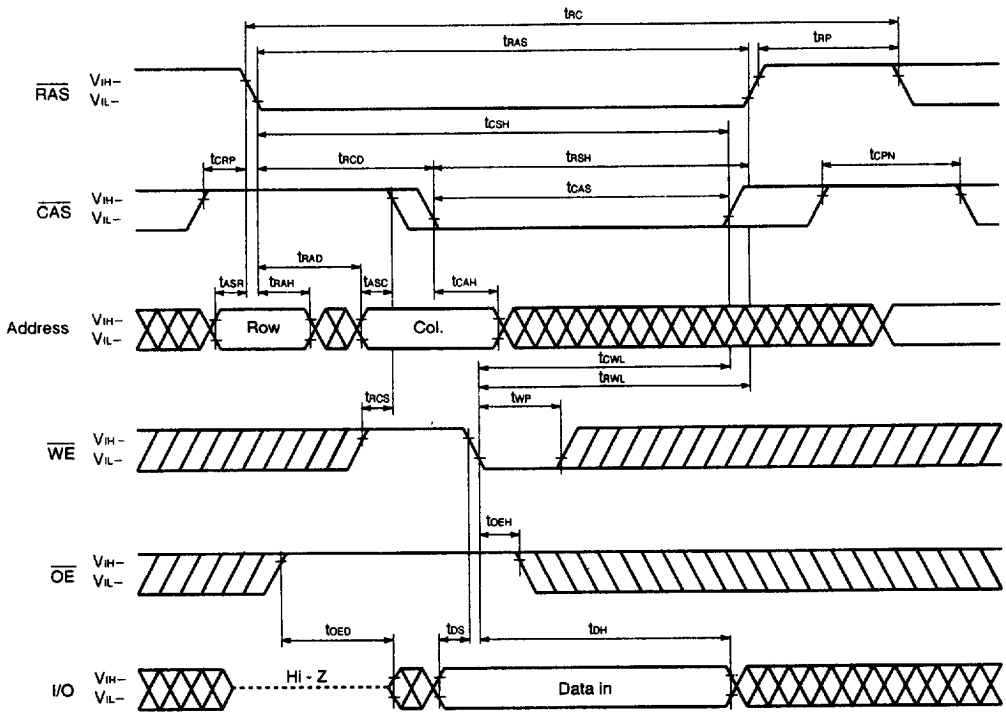


Early Write Cycle

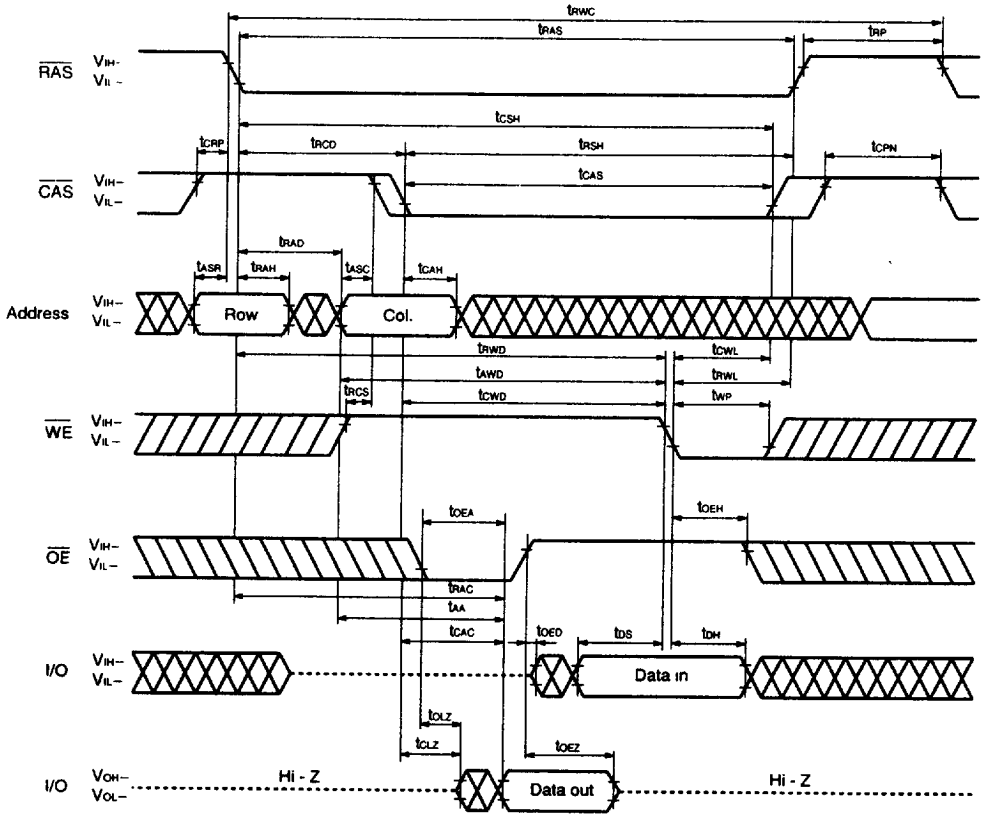


Remark $\overline{OE}$: Don't care

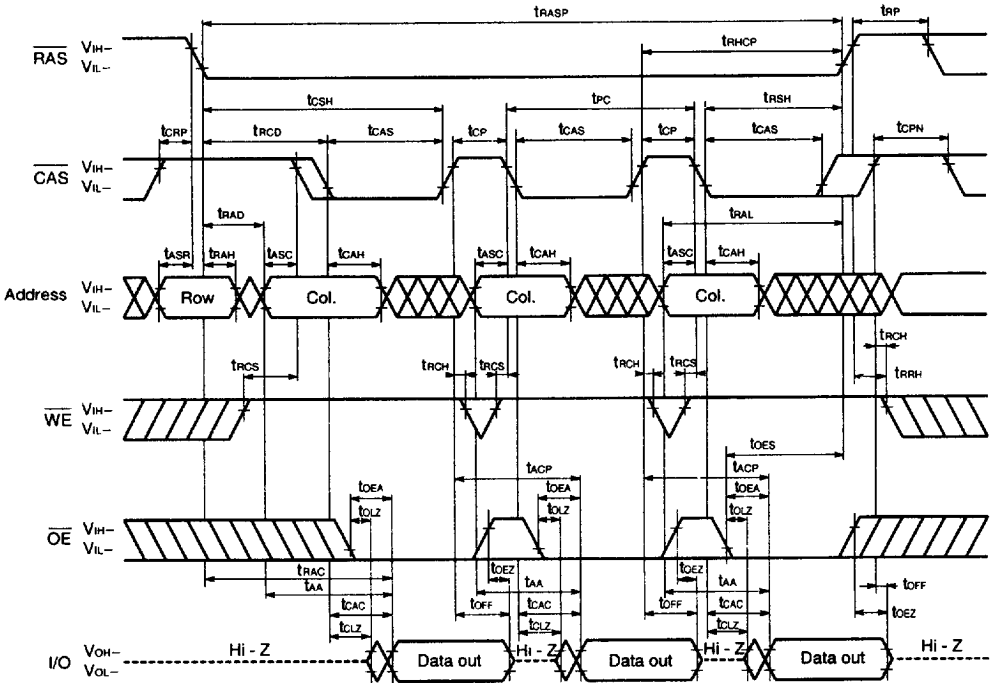
Late Write Cycle



Read Modify Write Cycle

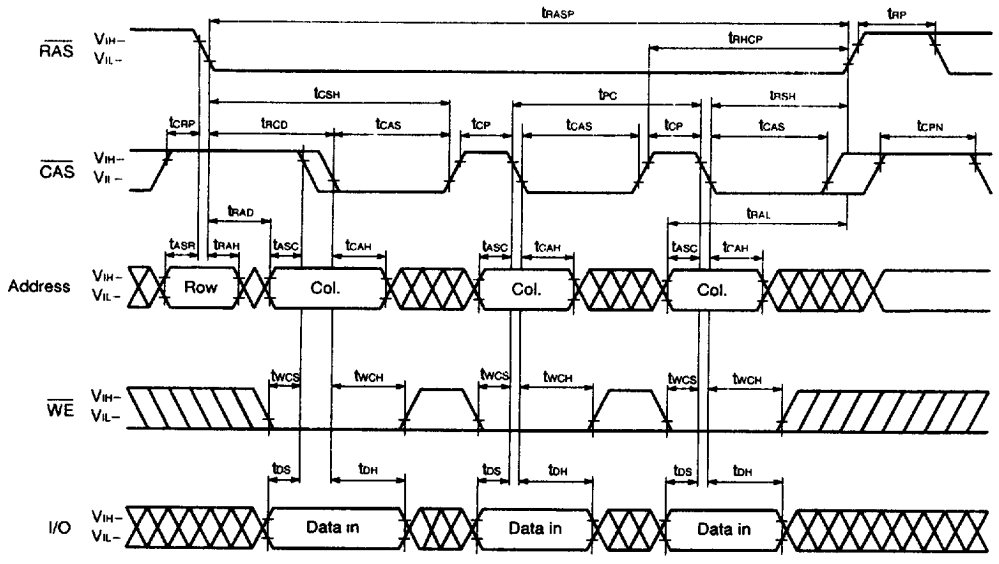


Fast Page Mode Read Cycle



Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

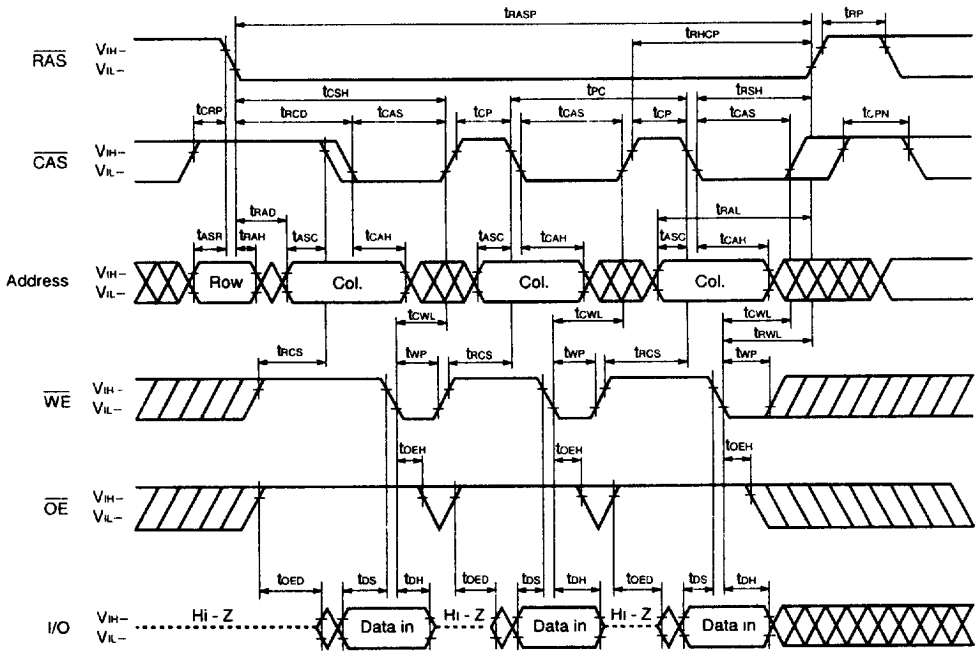
Fast Page Mode Early Write Cycle



Remark $\overline{OE}$: Don't care

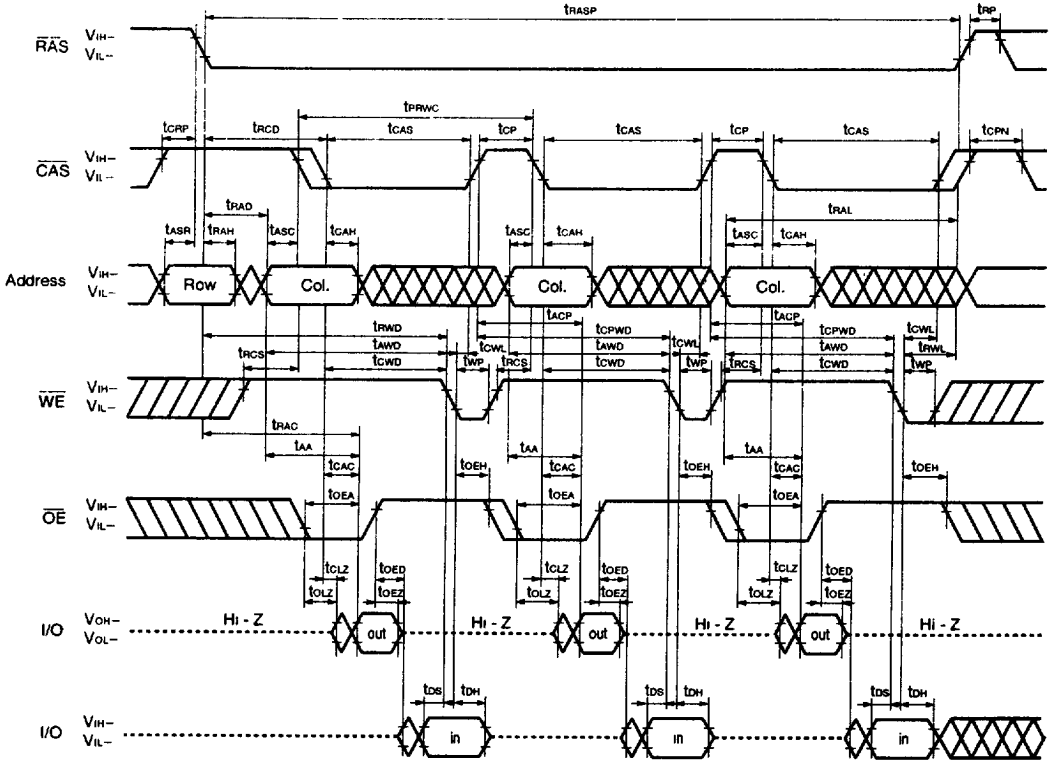
In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Fast Page Mode Late Write Cycle



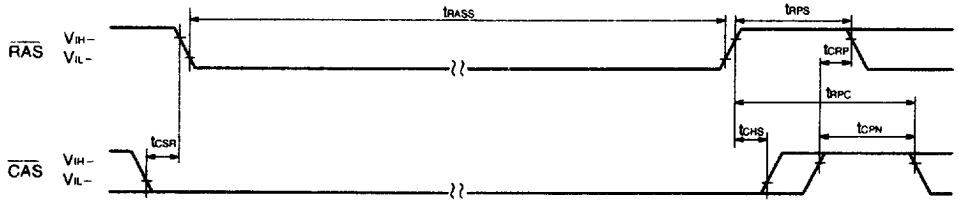
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Fast Page Mode Read Modify Write Cycle



Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

$\overline{CAS}$ Before $\overline{RAS}$ Self Refresh Cycle (Only for the μPD42S4800L)



Remark Address, $\overline{WE}$, $\overline{OE}$: Don't care I/O : Hi - Z

Cautions on Use of $\overline{CAS}$ Before $\overline{RAS}$ Self Refresh

$\overline{CAS}$ before $\overline{RAS}$ self refresh can be used independently when used in combination with distributed $\overline{CAS}$ before $\overline{RAS}$ long refresh; However, when used in combination with burst $\overline{CAS}$ before $\overline{RAS}$ long refresh or with burst long $\overline{RAS}$ only refresh, the following cautions must be observed.

(1) Normal Combined Use of $\overline{CAS}$ Before $\overline{RAS}$ Self Refresh and Burst $\overline{CAS}$ Before $\overline{RAS}$ Long Refresh

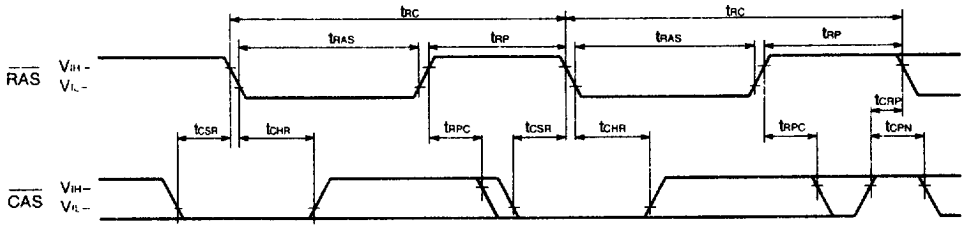
When $\overline{CAS}$ before $\overline{RAS}$ self refresh and burst $\overline{CAS}$ before $\overline{RAS}$ long refresh are used in combination, please perform $\overline{CAS}$ before $\overline{RAS}$ refresh 1 024 times within a 16 ms interval just before and after setting $\overline{CAS}$ before $\overline{RAS}$ self refresh.

(2) Normal Combined Use of $\overline{CAS}$ Before $\overline{RAS}$ Self Refresh and Burst Long $\overline{RAS}$ Only Refresh

When $\overline{CAS}$ before $\overline{RAS}$ self refresh and burst $\overline{RAS}$ only refresh are used in combination, please perform $\overline{RAS}$ only refresh 1 024 times within an interval of 16 ms or less just before and after setting $\overline{CAS}$ before $\overline{RAS}$ self refresh.

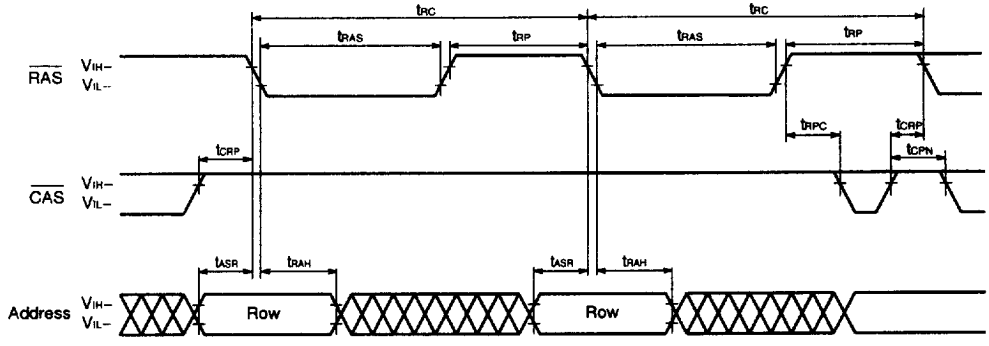
For details, please refer to **How to use DRAM** User's Manual.

$\overline{CAS}$ Before $\overline{RAS}$ Refresh Cycle



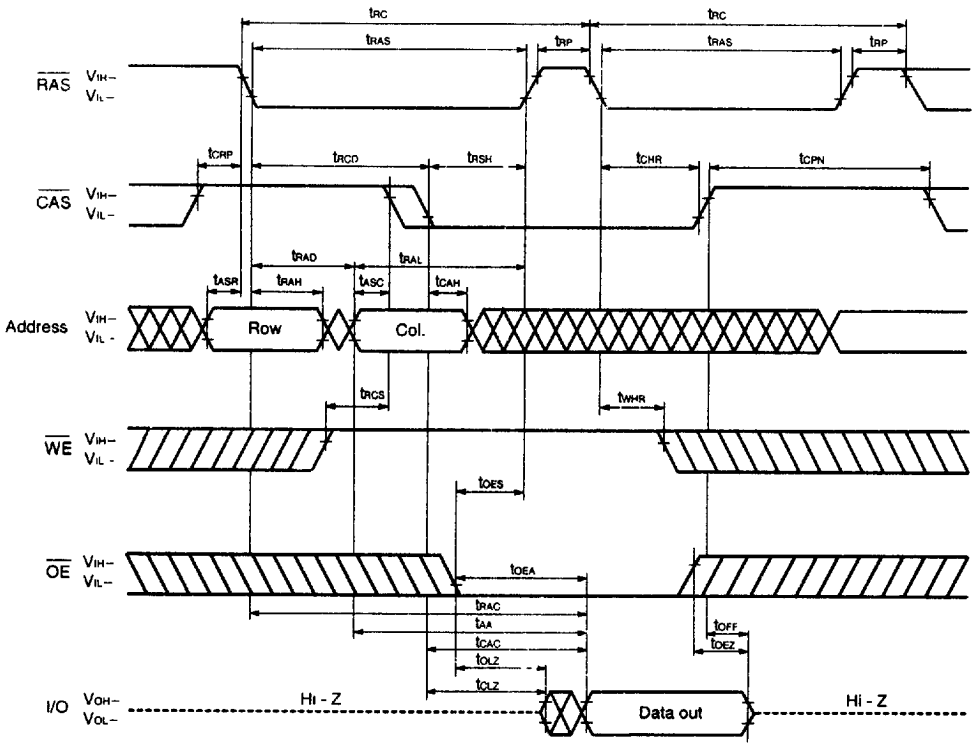
Remark Address, $\overline{WE}$, $\overline{OE}$: Don't care I/O : Hi - Z

$\overline{RAS}$ Only Refresh Cycle

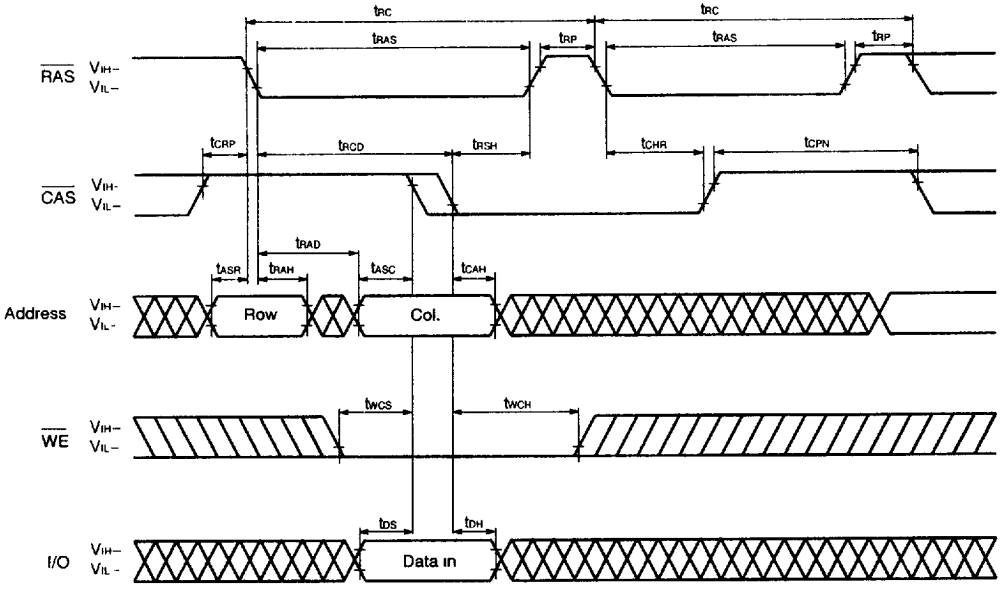


Remark $\overline{WE}$, $\overline{OE}$: Don't care I/O : Hi - Z

Hidden Refresh Cycle (Read)



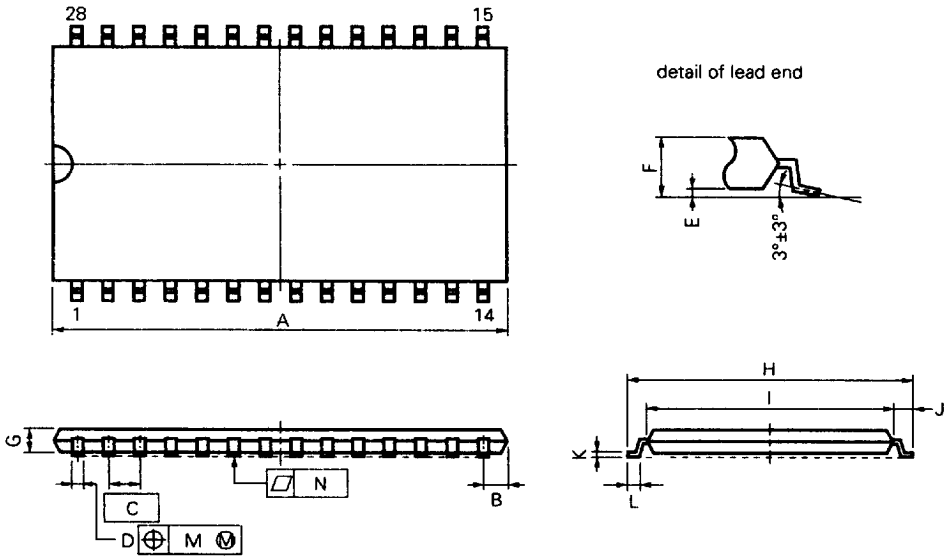
Hidden Refresh Cycle (Write)



Remark $\overline{OE}$: Don't care

Package Drawings

28 PIN PLASTIC TSOP(II) (400 mil)



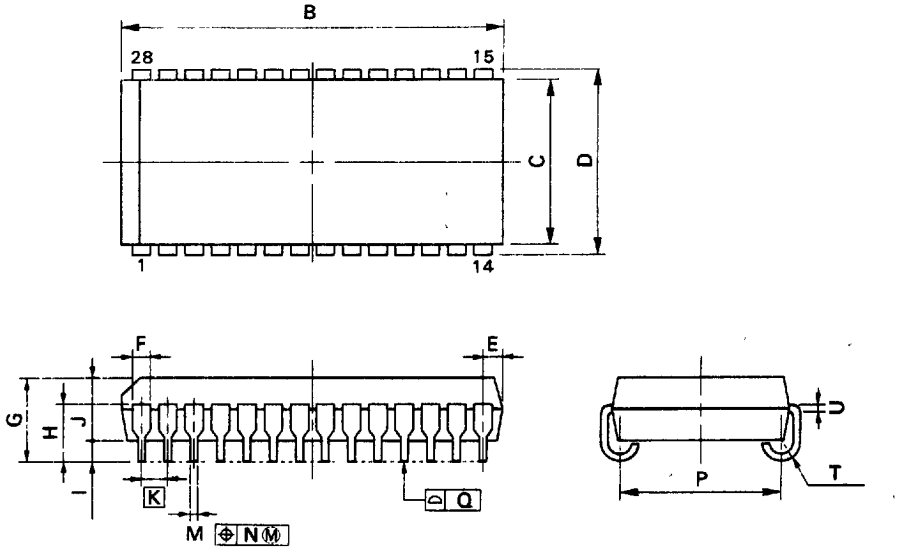
S28G5-50-7JD-2

NOTE

Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition

ITEM	MILLIMETERS	INCHES
A	18.81 MAX.	0.741 MAX.
B	1.15 MAX.	0.046 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.40±0.10	$0.016^{+0.004}_{-0.005}$
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	$0.031^{+0.009}_{-0.008}$
K	$0.125^{+0.10}_{-0.05}$	$0.005^{+0.004}_{-0.002}$
L	0.5±0.1	$0.020^{+0.004}_{-0.005}$
M	0.21	0.009
N	0.10	0.004

28PIN PLASTIC SOJ (400 mil)



P28LA-400A-1

NOTE
Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
B	$18.67^{+0.2}_{-0.35}$	$0.735^{+0.008}_{-0.013}$
C	10.16	0.400
D	$11.18^{\pm 0.2}$	$0.440^{+0.008}_{-0.009}$
E	$1.08^{\pm 0.16}$	$0.043^{+0.006}_{-0.007}$
F	0.6	0.024
G	$3.5^{\pm 0.2}$	$0.138^{+0.008}_{-0.009}$
H	$2.4^{\pm 0.2}$	$0.094^{+0.008}_{-0.009}$
I	0.8 MIN.	0.031 MIN.
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	$0.40^{\pm 0.10}$	$0.016^{+0.004}_{-0.005}$
N	0.12	0.005
P	$9.40^{\pm 0.20}$	$0.370^{+0.008}_{-0.009}$
Q	0.15	0.006
T	R0.85	R0.033
U	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$

Recommended Soldering Conditions

The following conditions (see tables below and next page) must be met for soldering conditions of the μPD42S4800L, 424800L.

For more details, refer to our document "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (IEI-1207).

Please consult with our sales offices in case other soldering process is used, or in case the soldering is done under different conditions.

Types of Surface Mount Device

μPD42S4800LG5, 424800LG5 : 28-pin plastic TSOP(II) (400 mil)

Soldering process	Soldering conditions	Symbol
Infrared ray reflow	Peak temperature of package surface : 235 °C or below, Reflow time: 30 seconds or below (210 °C or higher), Number of reflow processes: MAX. 2 Exposure limit[Note]: 7 days (10 hours pre-baking is required at 125 °C afterwards) **[Remark]** (1) Please start the second reflow process after the temperature, raised by the first reflow process, returns to normal. (2) Please avoid removing the residual flux with water after the first reflow process .	IR35-107-2
VPS	Peak temperature of package : 215 °C or below, Reflow time : 40 seconds or below (200 °C or higher), Number of reflow processes: MAX. 2 Exposure limit[Note]: 7 days (10 hours pre-baking is required at 125 °C afterwards) **[Remark]** (1) Please start the second reflow process after the temperature, raised by the first reflow process, returns to normal. (2) Please avoid removing the residual flux with water after the first reflow process .	VP15-107-2
Partial heating method	Terminal temperature: 300 °C or below, Time : 3 seconds or below (Per one side of the device).	————

Note Exposure limit before soldering after dry-pack package is opened.
Storage conditions: 25 °C and relative humidity at 65 % or less.

Caution Do not apply more than one soldering method at any one time, except for "Partial heating method".

μPD42S4800LLE, 424800LLE : 28-pin plastic SOJ (400 mil)

Soldering process	Soldering conditions	Symbol
Infrared ray reflow	Peak temperature of package surface : 235 °C or below, Reflow time: 30 seconds or below (210 °C or higher), Number of reflow processes: MAX. 2 Exposure limit[Note]: 7 days (20 hours pre-baking is required at 125 °C afterwards) **[Remark]** (1) Please start the second reflow process after the temperature, raised by the first reflow process, returns to normal. (2) Please avoid removing the residual flux with water after the first reflow process.	IR35-207-2
VPS	Peak temperature of package . 215 °C or below, Reflow time : 40 seconds or below (200 °C or higher), Number of reflow processes: MAX. 2 Exposure limit[Note]: 7 days (20 hours pre-baking is required at 125 °C afterwards) **[Remark]** (1) Please start the second reflow process after the temperature, raised by the first reflow process, returns to normal. (2) Please avoid removing the residual flux with water after the first reflow process.	VP15-207-2
Partial heating method	Terminal temperature: 300 °C or below, Time : 3 seconds or below (Per one side of the device).	———

Note Exposure limit before soldering after dry-pack package is opened.
Storage conditions: 25 °C and relative humidity at 65 % or less.

Caution Do not apply more than one soldering method at any one time, except for "Partial heating method".